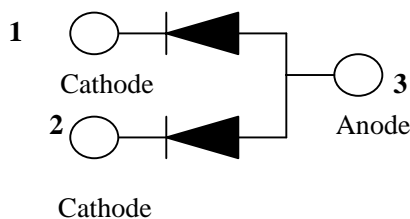




Switching Diode (FHD56)



开关二极管

MAXIMUM RATINGS 最大额定值

Rating 额定值	Symbol 符号	Value 值	Unit 单位
Continuous Reverse Voltage 连续反向电压	V_R	70	Vdc
Peak Forward Current 正向峰值电流	I_F	200	mAdc
Peak Forward Surge Current 正向最大浪涌电流	$I_{FM(surge)}$	500	mAdc

THERMAL CHARACTERISTICS 热特性

Characteristic 特性	Symbol 符号	Max 最大值	Unit 单位
Total Device Dissipation FR-5 Board(1) $T_A=25$	P_D	225	mW
Total Device Dissipation Alumina Substrate,(2) $T_A=25$ 总耗散功率 氧化铝衬底	P_D	300	mW
Junction and Storage Temperature 结温和储存温度	T_J, T_{stg}	150, -55 to +150	

DEVICE MARKING 打标

FHD56=A1

ELECTRICAL CHARACTERISTICS 电特性 ($T_A=25$ unless otherwise noted 如无特殊说明, 温度为 25)

Characteristic 特性	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
-------------------	-----------	---------	---------	---------

OFF CHARACTERISTICS 截止电特性

Reverse Voltage Leakage Current 反向漏电流($V_R=70Vdc$) ($V_R=70Vdc, T_j=150$) ($V_R=25Vdc, T_j=150$)	I_R	—	2.5 50 30	μA_{dc}
Reverse Breakdown Voltage 反向击穿电压($I_{BR}=100 \mu A_{dc}$)	$V_{(BR)}$	70	—	Vdc
Forward Voltage 正向电压 ($I_F=1mA_{dc}$) ($I_F=10mA_{dc}$) ($I_F=50mA_{dc}$) ($I_F=150mA_{dc}$)	V_F	—	715 855 1000 1250	mVdc
Diode Capacitance 电容($V_R=0, f=1.0MHz$)	C_D	—	2.0	pF
Reverse Recovery Time 反向恢复时间($I_F=I_R=10mA_{dc}, R_L=50$)	t_{rr}	—	6.0	ns

- FR-5=1.0 × 0.75 × 0.062 in.
- Alumina=0.4 × 0.3 × 0.024 in. 99.5% alumina.